



# ADH451S Data Sheet Limit Revision

# Data Sheet Specification Comparison

## Rev C

## Rev D

### 4.0 Specifications

#### 4.1. Absolute Maximum Ratings 1/

|   |                       |
|---|-----------------------|
| Drain Bias Voltage (Vdd1 = Vdd2) .....                                      | 5.5 V <u>2/</u>       |
| RF Input Power (RFIN) (Vdd1 = Vdd2 = +5V) .....                             | +10 dBm               |
| Channel Temperature .....   | +175 °C               |
| Continuous P <sub>diss</sub> (T = +85 °C) (Derate 9.29mW/°C above +85 °C) . | 0.836 W               |
| Thermal resistance (Channel to package bottom) .....                        | 107.64 °C/W           |
| Storage temperature range .....   | -65 °C to +150 °C     |
| ESD Sensitivity (HBM) .....   | Class 1A, passed 250V |

### 4.0 Specifications

#### 4.1. Absolute Maximum Ratings 1/

|  |                                  |
|--|----------------------------------|
| Drain Bias Voltage (Vdd1 = Vdd2) .....   | 5.5 V <u>2/</u>                  |
| RF Input Power (RFIN) (Vdd1 = Vdd2 = +5V) .....  | +10 dBm                          |
| Channel Temperature .....  | +175 °C                          |
| Continuous P <sub>diss</sub> (T = +85 °C) (Derate <del>9.29mW/°C</del> <sup>17.36mW/°C</sup> above +85 °C) . | <del>0.836 W</del> 1.563 W       |
| Thermal resistance (Channel to package bottom) .....   | <del>107.64 °C/W</del> 57.6 °C/W |
| Storage temperature range .....  | -65 °C to +150 °C                |
| ESD Sensitivity (HBM) .....  | Class 1A, passed 250V            |